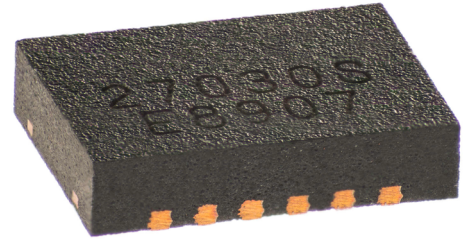


CGH27030S

30 W, DC - 6.0 GHz, 28 V, GaN HEMT



Package Type: 3x4 DFN
PN: CGH27030S

Description

The CGH27030S is an unmatched, gallium nitride (GaN) high electron mobility transistor (HEMT) designed specifically for high efficiency, high gain and wide bandwidth capabilities, which makes the CGH27030S ideal for LTE, 4G Telecom and BWA amplifier applications. The CGH27030S operates from a 28 volt rail. The transistor is available in a 3mm x 4mm, surface mount, dual-flat-no-lead (DFN) package.

Typical Performance 1.8-2.7 GHz ($T_c = 25^\circ\text{C}$), 28 V

Parameter	1.8 GHz ¹	2.0 GHz ¹	2.2 GHz ¹	2.3 GHz ²	2.5 GHz ²	2.7 GHz ²	Units
Small Signal Gain	20.0	20.4	19.5	21.1	20.6	20.0	dB
Adjacent Channel Power @ $P_{AVE} = 5\text{ W}$	-39.5	-42.1	-39.1	-32.0	-36.4	-33.6	dBc
Drain Efficiency @ $P_{AVE} = 5\text{ W}$	31.8	32.8	33.8	37.8	36.2	35.0	%
Input Return Loss	-4.2	-6.4	-7.7	-7.3	-7.9	-7.2	dB

Notes:

¹ Measured in the CGH27030S-AMP1 amplifier circuit, under 7.5 dB PAR single carrier WCDMA signal test model 1 with 64 DPCH

² Measured in the CGH27030S-AMP2 amplifier circuit, under 7.5 dB PAR single carrier WCDMA signal test model 1 with 64 DPCH

Features for 28 V in CGH27030S-AMP1

- 1.8 - 2.2 GHz Operation
- 30 W Typical Output Power
- 18 dB Gain at 5 W P_{AVE}
- -39 dBc ACLR at 5 W P_{AVE}
- 33% efficiency at 5 W P_{AVE}
- High degree of APD and DPD correction can be applied

Features for 28 V in CGH27030S-AMP2

- 2.3 - 2.7 GHz Operation
- 30 W Typical Output Power
- 18.5 dB Gain at 5 W P_{AVE}
- -39 dBc ACLR at 5 W P_{AVE}
- 36% efficiency at 5 W P_{AVE}
- High degree of APD and DPD correction can be applied

 Large Signal Models Available for ADS and MWO



Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V_{DSS}	120	V	25°C
Gate-to-Source Voltage	V_{GS}	-10, +2		
Storage Temperature	T_{STG}	-65, +150	°C	
Operating Junction Temperature	T_J	225		
Maximum Forward Gate Current	I_{GMAX}	7.2	mA	25°C
Maximum Drain Current ¹	I_{DMAX}	3.0		
Soldering Temperature ²	T_S	245	°C	
Case Operating Temperature ³	T_C	-40, +150		
Thermal Resistance, Junction to Case ^{4,5}	$R_{\theta JC}$	3.65	°C/W	85°C

Notes:

¹ Current limit for long term, reliable operation

² Refer to the Application Note on soldering

³ T_C = Case temperature for the device. It refers to the temperature at the ground tab underneath the package. The PCB will add additional thermal resistance

⁴ Simulated for the CGH27030S at $P_{DISS} = 21.6$ W

⁵ The R_{TH} for the demonstration amplifier, CGH27030S-AMP1, with 33 x 0.011 via holes designed on a 20 mil thick Rogers 4350 PCB, is 3.51°C. The total R_{TH} from the heat sink to the junction is 3.62°C + 3.51°C = 7.13 °C/W

Electrical Characteristics ($T_C = 25^\circ\text{C}$)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics¹						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	$V_{DS} = 10$ V, $I_D = 7.2$ mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-2.7	–		$V_{DS} = 28$ V, $I_D = 0.20$ A
Saturated Drain Current	I_{DS}	5.0	7.0	–	A	$V_{DS} = 6.0$ V, $V_{GS} = 2.0$ V
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	84	–	–	V_{DC}	$V_{GS} = -8$ V, $I_D = 7.2$ mA
RF Characteristics³ ($T_C = 25^\circ\text{C}$, $F_0 = 2.65$ GHz unless otherwise noted)						
Gain	G	17.8	19.1	–	dB	$V_{DD} = 28$ V, $I_{DQ} = 0.20$ A, $P_{IN} = 10$ dBm
Output Power	P_{OUT}	44.3	44.9	–	dBm	$V_{DD} = 28$ V, $I_{DQ} = 0.20$ A, $P_{IN} = 30$ dBm
Drain Efficiency ³	η	65	72	–	%	
Output Mismatch Stress	VSWR	–	–	10:1	Ψ	No damage at all phase angles, $V_{DD} = 28$ V, $I_{DQ} = 0.20$ A, $P_{IN} = 30$ dBm
Dynamic Characteristics						
Input Capacitance ⁴	C_{GS}	–	8.6	–	pF	$V_{DS} = 28$ V, $V_{GS} = -8$ V, $f = 1$ MHz
Output Capacitance ⁴	C_{DS}	–	2.0	–		
Feedback Capacitance	C_{GD}	–	0.4	–		

Notes:

¹ Measured on wafer prior to packaging

² Measured in the production test fixture. This fixture is designed for high volume test at 2.65 GHz

³ Un-modulated Pulsed Signal, 100 μ s, 10% duty cycle

⁴ Includes package and internal matching components

Typical Performance in CGH27030S-AMP1

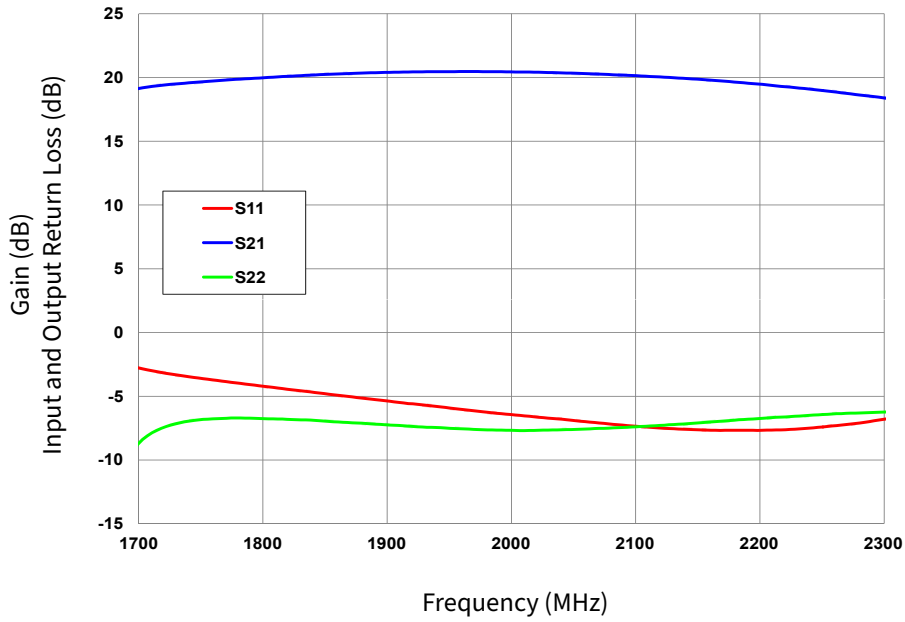


Figure 1. Small Signal Gain and Return Losses vs Frequency
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 0.20\text{ A}$

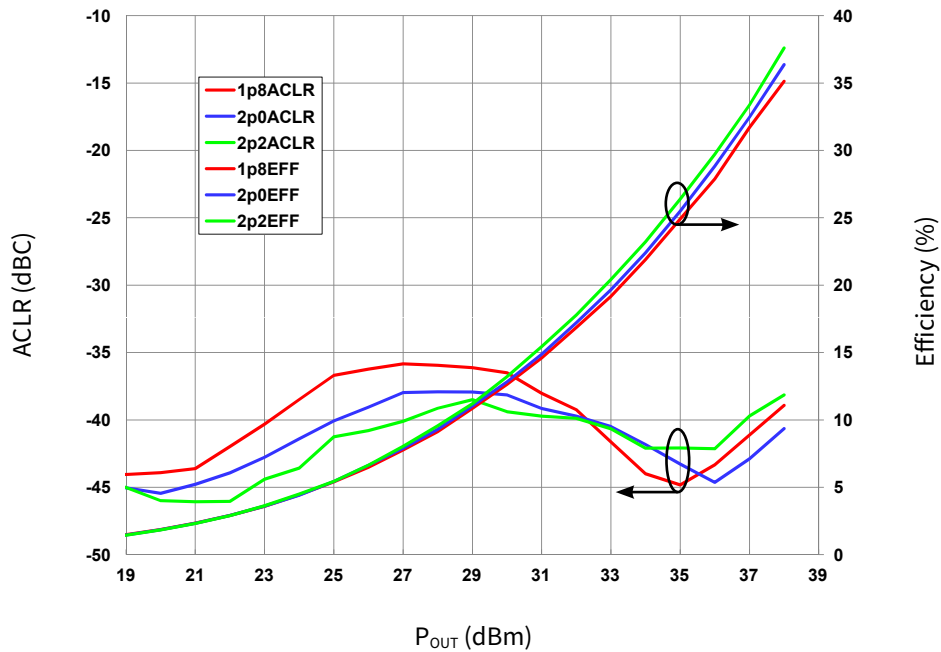


Figure 2. Typical Drain Efficiency and ACLR vs Output Power
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 0.20\text{ A}$, 1c WCDMA, PAR = 7.5 dB

Typical Performance in CGH27030S-AMP1

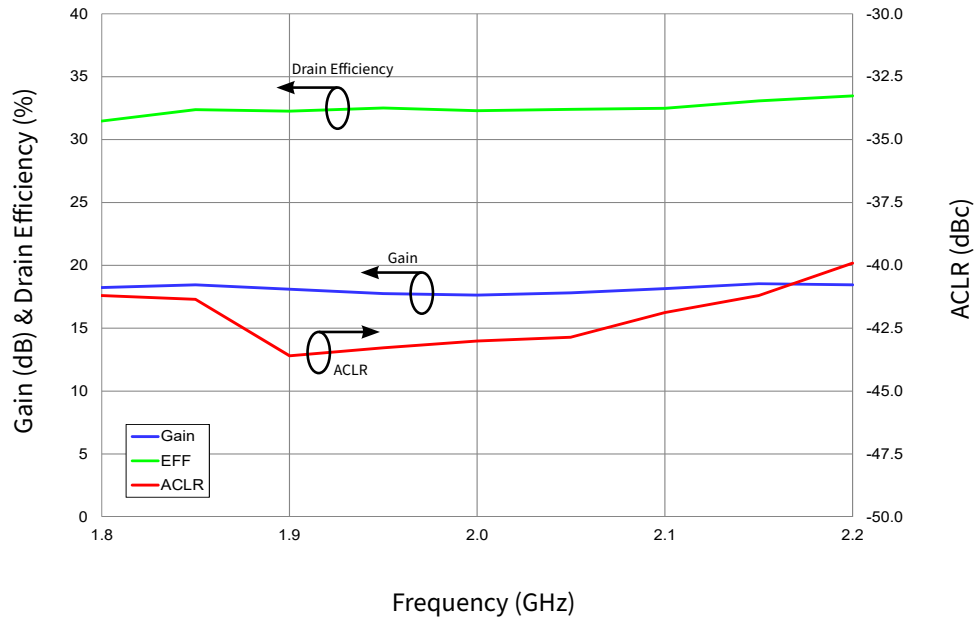
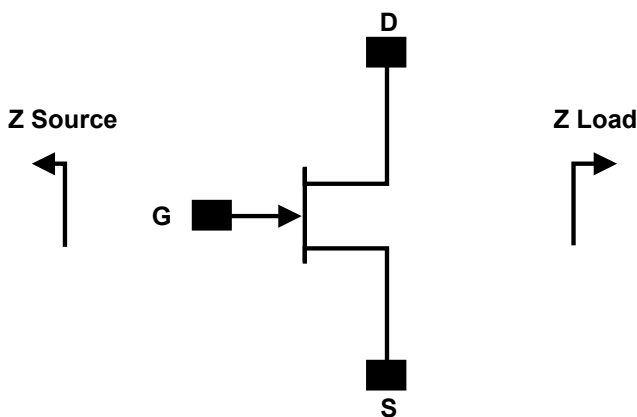


Figure 3. Typical Gain, Drain Efficiency and ACLR vs Frequency
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 0.20\text{ A}$, $P_{AVE} = 5\text{ W}$, 1c WCDMA, PAR = 7.5 dB

Source and Load Impedances for Application Circuit CGH27030S-AMP1



Frequency	Z Source	Z Load
1800	3.5 - j1.6	11 + j0.2
2000	3.6 - j0.6	10.5 - j1.8
2200	3.3 - j0.1	11 + j3.3

Notes:

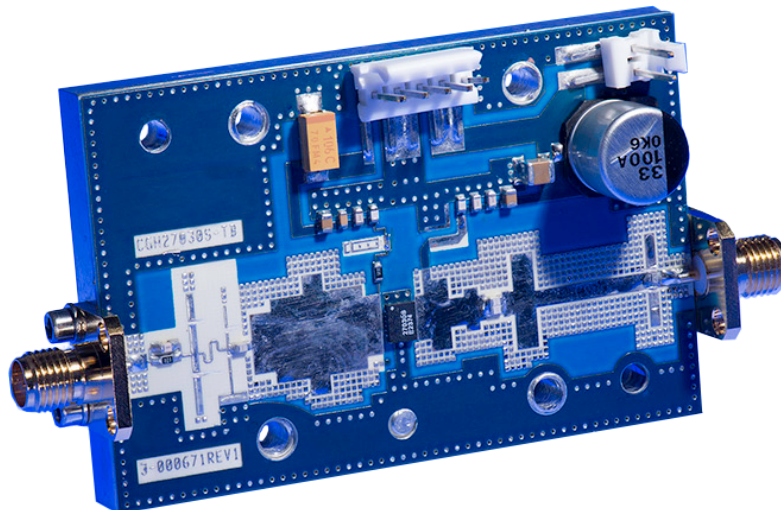
¹ $V_{DD} = 28\text{ V}$, $I_{DQ} = 0.20\text{ A}$ in the DFN package

² Impedances are extracted from the CGH27030S-AMP1 application circuit and are not source and load pull data derived from the transistor

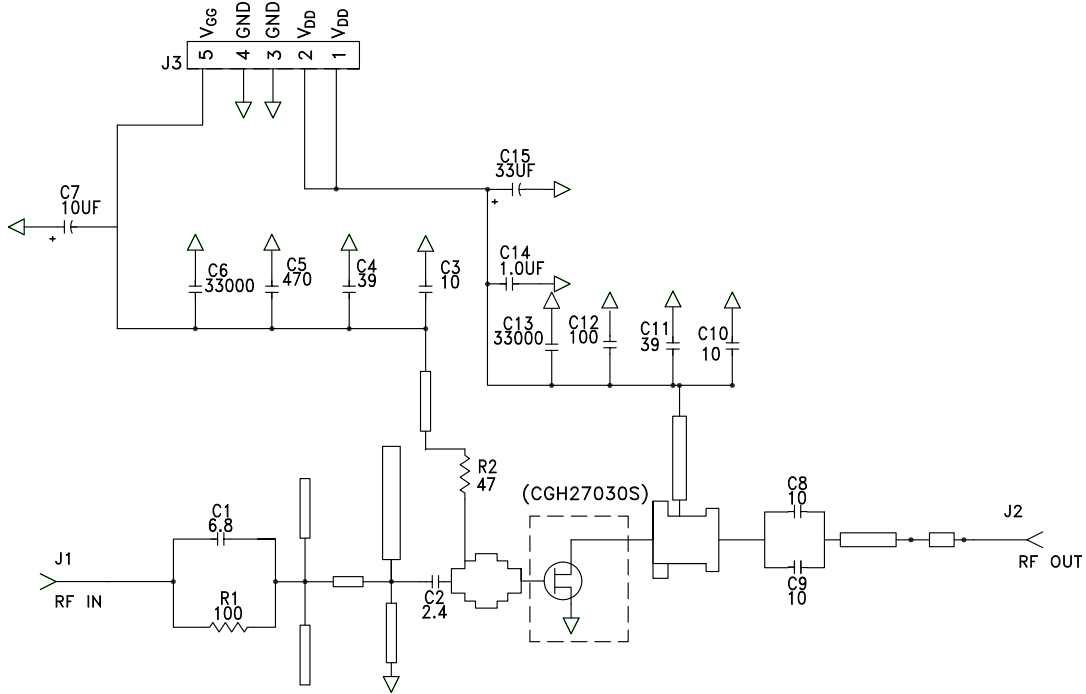
CGH27030S-AMP1 Application Circuit Bill of Materials

Designator	Description	Qty
R1	RES, 1/16 W, 0603, 1%, 100 OHMS	1
R2	RES, 1/16 W, 0603, 1%, 5.1 OHMS	1
C1	CAP, 6.8pF, ± 0.25 pF, 0603, ATC	1
C2	CAP, 2.4pF, ± 0.01 pF, 0603, ATC	1
C3, C8, C9, C10	CAP, 10.0pF, ± 0.5 pF, 0603, ATC	3
C12	CAP, 100.0pF, 5%, 0603, ATC	1
C5	CAP, 470pF, 5%, 100 V, 0603	1
C6, C13	CAP, 33000pF, 0805, 10%, 100 V, X7R	2
C14	CAP, 1.0 μ F, 100 V, 10%, X7R, 1210	1
C7	CAP, 10 μ F, 16 V, TANTALUM	1
C15	CAP, 33 μ F, 20%, G CASE	1
J1, J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST	2
Q1	CGH27030S, QFN	1

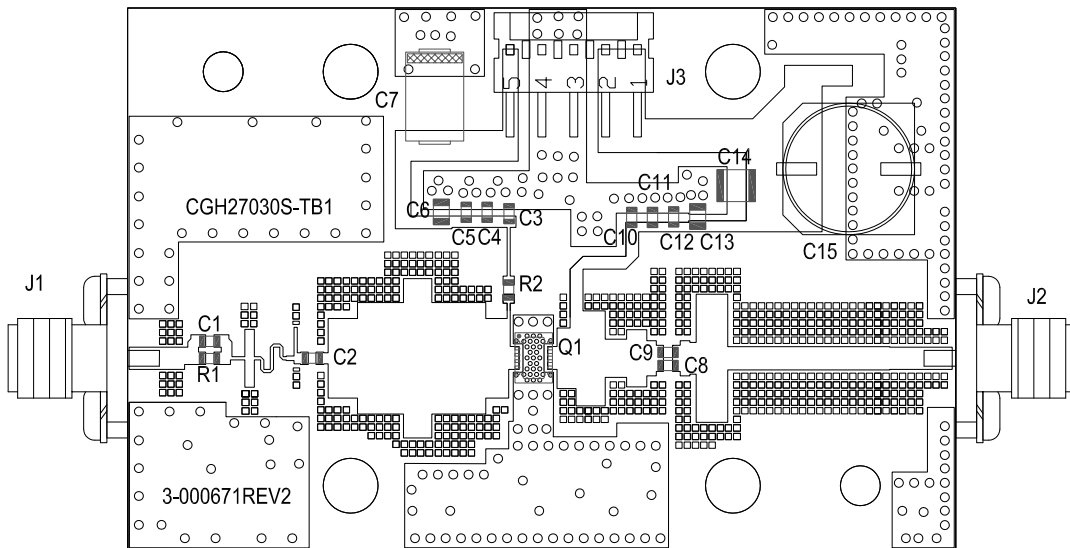
CGH27030S-AMP1 Application Circuit, 28 V, 1.8 - 2.2 GHz



CGH27030S-AMP1 Application Circuit Schematic, 28 V, 1.8 - 2.2 GHz



CGH27030S-AMP1 Application Circuit, 28 V, 1.8 - 2.2 GHz



Typical Performance in Application Circuit CGH27030S-AMP2

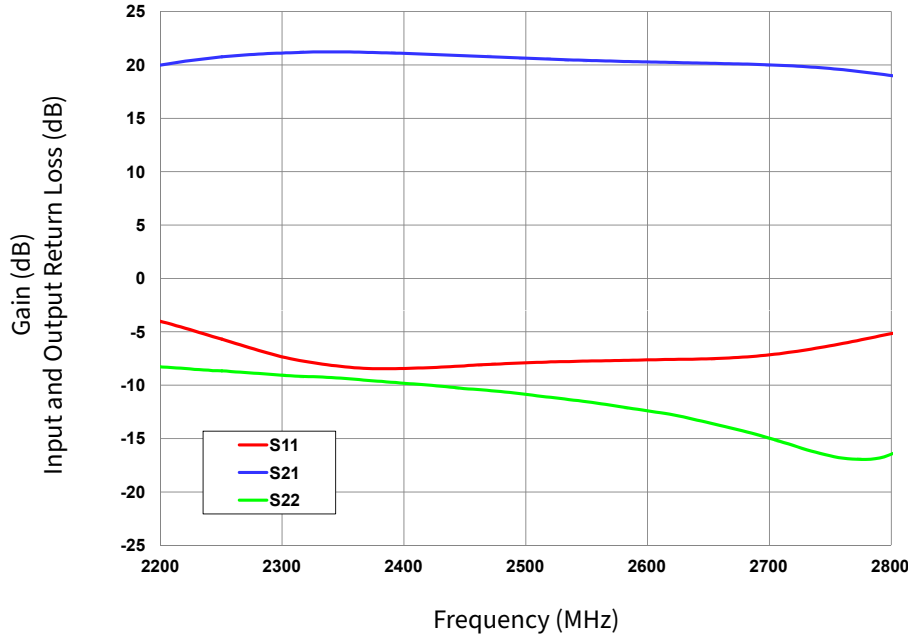


Figure 4. Small Signal Gain and Return Losses vs Frequency
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 0.20\text{ A}$

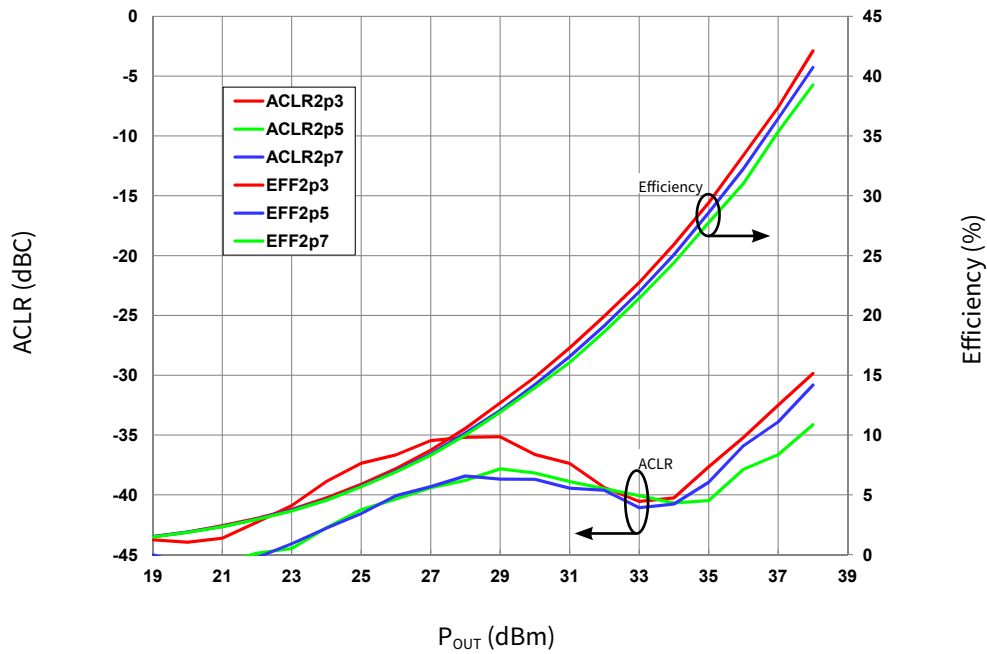


Figure 5. Typical Drain Efficiency and ACLR vs Output Power
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 0.20\text{ A}$, 1c WCDMA, PAR = 7.5 dB

Typical Performance in Application Circuit CGH27030S-AMP2

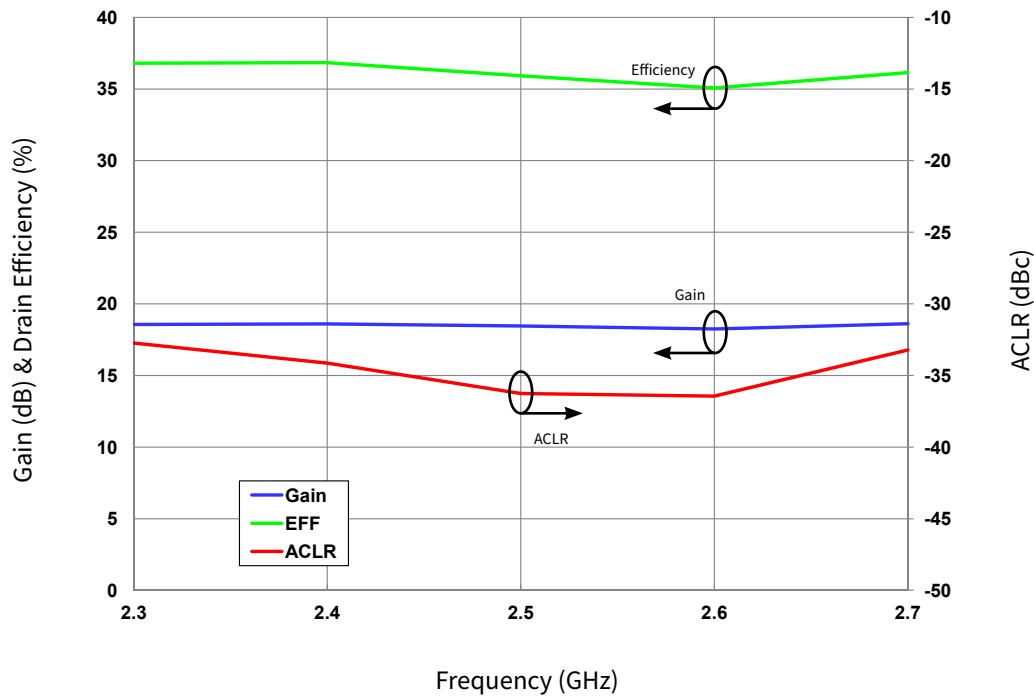


Figure 6. Typical Gain, Drain Efficiency and ACLR vs Frequency
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 0.20\text{ A}$, $P_{AVE} = 5\text{ W}$, 1c WCDMA, PAR = 7.5 dB

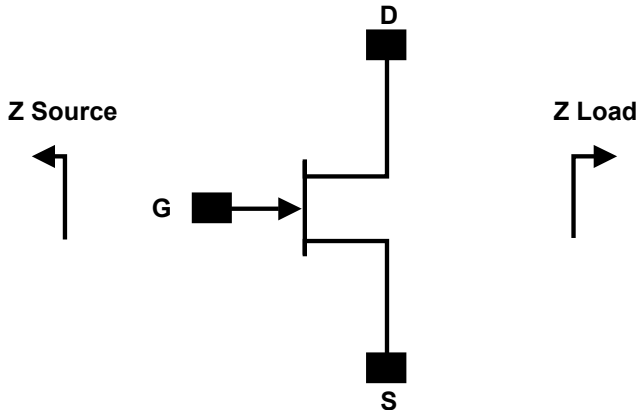
Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Classification Level	Test Methodology
Human Body Model	HBM	1B	ANSI/ESDA/JEDEC JS-001 Table 3	JEDEC JESD22 A114-D
Charge Device Model	CDM	C3	ANSI/ESDA/JEDEC JS-002 Table 3	JEDEC JESD22 C101-C

Moisture Sensitivity Level (MSL) Classification

Parameter	Symbol	Level	Test Methodology
Moisture Sensitivity Level	MSL	3 (168 hours)	IPC/JEDEC J-STD-20

Source and Load Impedances for Application Circuit CGH27030S-AMP2



Frequency	Z Source	Z Lead
2300	1.7 - j0.5	7.7 + j7.7
2500	2.2 - j0.2	8.0 + j6.8
2700	1.5 - j0.1	6.6 + j6.3

Notes:

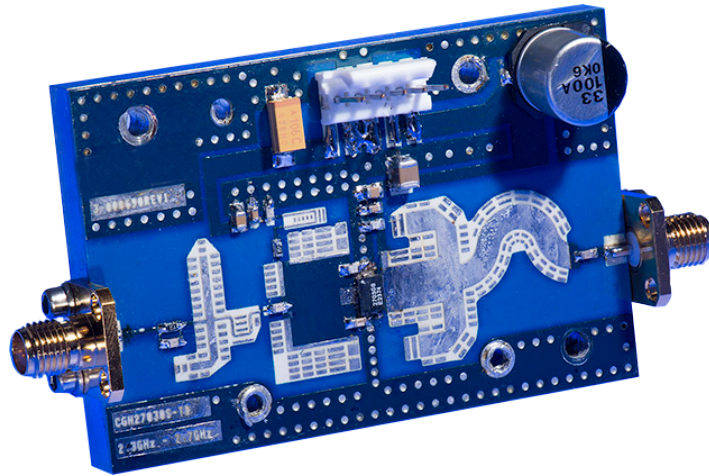
¹ $V_{DD} = 28\text{ V}$, $I_{DQ} = 0.20\text{ A}$ in the DFN package

² Impedances are extracted from the CGH27030S-AMP2 application circuit and are not source and load pull data derived from the transistor

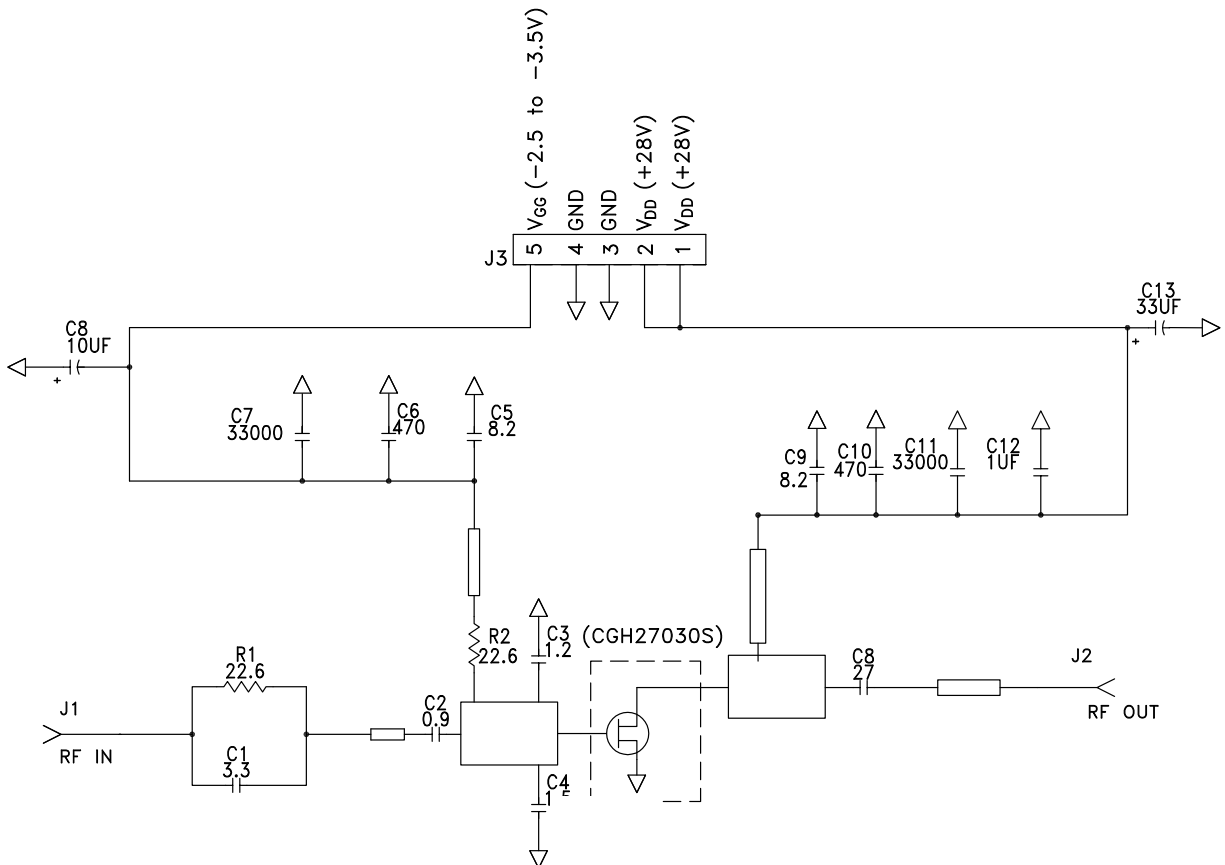
CGH27030S-AMP1 Application Circuit Bill of Materials

Designator	Description	Qty
R1, R2	RES, 22.6, OHM, +/-1%, 1/16W, 0603	2
C1	CAP, 3.3pF, ±0.1pF, 0603, ATC	1
C2	CAP, 0.9pF, ±0.1pF, 0603, ATC	1
C3	CAP, 1.2pF, ±0.1pF, 0603, ATC	1
C4	CAP, 1.5pF, ±0.1pF, 0603, ATC	1
C5, C9	CAP, 8.2pF, ±0.25pF, 0603, ATC	2
C6, C10	CAP, 470pF, 5%, 100 V, 0603, X	2
C7, C11	CAP, 33000pF, 0805, 100 V, X7R	2
C12	CAP, 1.0μF, 100 V, 10%, X7R, 1210	1
C8	CAP, 10μF 16 V TANTALUM	1
C14	CAP, 27pF, ±5%, 0603, ATC	1
C13	CAP, 33μF, 20%, G CASE	1
J1, J2	CONN, SMA, PANEL MOUNT JACK, FLANGE, 4-HOLE, BLUNT POST	1
Q1	CGH27030S, QFN	2

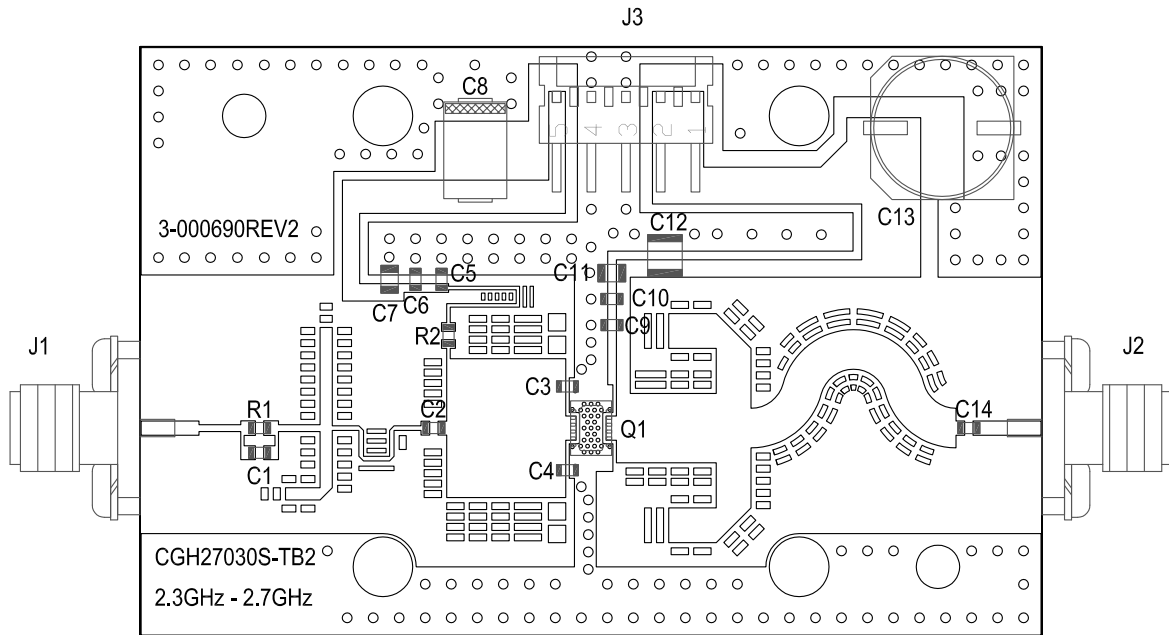
CGH27030S-AMP2 Application Circuit, 28 V, 2.3 - 2.7 GHz



CGH27030S-AMP2 Application Circuit Schematic, 28 V, 2.3 - 2.7 GHz

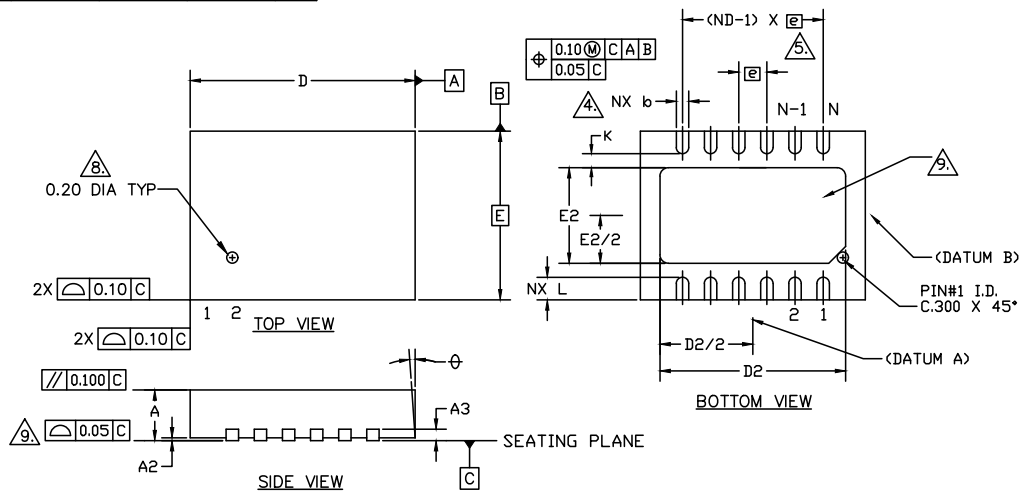


CGH27030S-AMP2 Application Circuit, 28 V, 2.3 - 2.7 GHz

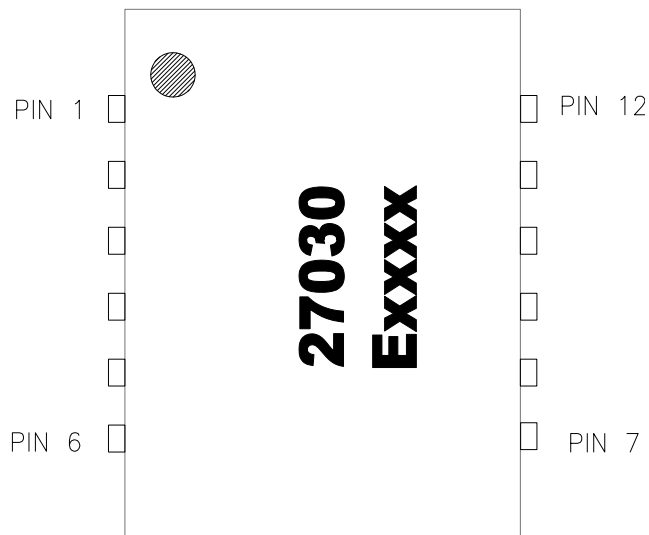


Product Dimensions CGH27030S (Package 3 x 4 DFN)

SYMBOL	COMMON DIMENSIONS			NOTE
	MIN.	NOM.	MAX.	
A	0.80	0.90	1.0	
A1	0.00	0.02	0.05	
A3	0.203 REF.			
Ø	0	—	12	2
D	4.00 BSC			
E	3.00 BSC			
Ⓢ	0.50 BSC			
N	12			3
ND	6			▲
L	0.35	0.40	0.45	
b	0.18	0.25	0.30	▲
D2	3.20	3.30	3.40	
E2	1.60	1.7	1.80	
K	0.20	—	—	



Pin	Input/Output
1	GND
2	RF IN
3	RF IN
4	RF IN
5	RF IN
6	GND
7	GND
8	RF OUT
9	RF OUT
10	RF OUT
11	RF OUT
12	GND



Note: Leadframe finish for 3x4 DFN package is Nickel/Palladium/Gold. Gold is the outer layer.

Part Number System

CGH27030S

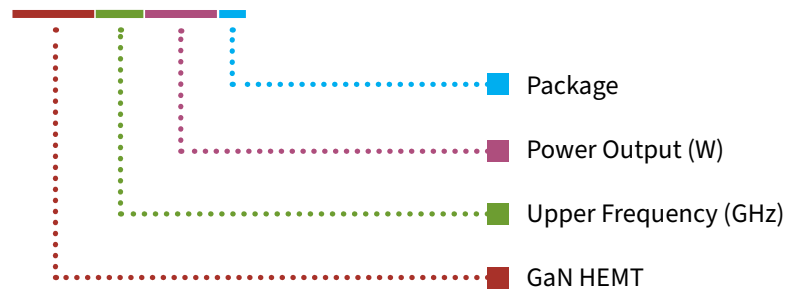


Table 1.

Parameter	Value	Units
Upper Frequency ¹	2.7	GHz
Power Output	30	W
Package	Surface Mount	—

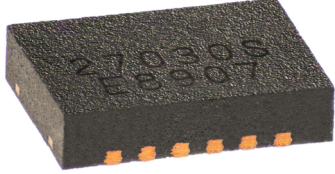
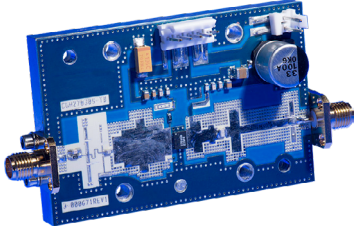
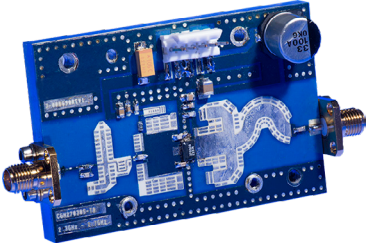
Note:

¹ Alpha characters used in frequency code indicate a value greater than 9.9 GHz. See Table 2 for value.

Table 2.

Character Code	Code Value
A	0
B	1
C	2
D	3
E	4
F	5
G	6
H	7
J	8
K	9
Examples	1A = 10.0 GHz 2H = 27.0 GHz

Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGH27030S	GaN HEMT	Each	
CGH27030S-AMP1	Test board with GaN HEMT installed	Each	
CGH27030S-AMP2	Test board with GaN HEMT installed	Each	

Notes & Disclaimer

MACOM Technology Solutions Inc. ("MACOM"). All rights reserved.

These materials are provided in connection with MACOM's products as a service to its customers and may be used for informational purposes only. Except as provided in its Terms and Conditions of Sale or any separate agreement, MACOM assumes no liability or responsibility whatsoever, including for (i) errors or omissions in these materials; (ii) failure to update these materials; or (iii) conflicts or incompatibilities arising from future changes to specifications and product descriptions, which MACOM may make at any time, without notice. These materials grant no license, express or implied, to any intellectual property rights.

THESE MATERIALS ARE PROVIDED "AS IS" WITH NO WARRANTY OR LIABILITY, EXPRESS OR IMPLIED, RELATING TO SALE AND/OR USE OF MACOM PRODUCTS INCLUDING FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, INFRINGEMENT OF INTELLECTUAL PROPERTY RIGHT, ACCURACY OR COMPLETENESS, OR SPECIAL, INDIRECT, INCIDENTAL, OR CONSEQUENTIAL DAMAGES WHICH MAY RESULT FROM USE OF THESE MATERIALS.

MACOM products are not intended for use in medical, lifesaving or life sustaining applications. MACOM customers using or selling MACOM products for use in such applications do so at their own risk and agree to fully indemnify MACOM for any damages resulting from such improper use or sale.